

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSVII)

TPCA8007-H

Switching Regulator Applications

Motor Drive Applications

- Small footprint due to small and thin package
- High speed switching
- Low drain-source ON resistance
: $R_{DS(ON)} = 30 \text{ m}\Omega$ (typ.) ($V_G = 10 \text{ V}$, $I_D = 10 \text{ A}$)
- High forward transfer admittance: $|Y_{fs}| = 19 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 100 \text{ }\mu\text{A}$ (max) ($V_{DS} = 100 \text{ V}$)
- Enhancement mode: $V_{th} = 3.0$ to 5.0 V ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

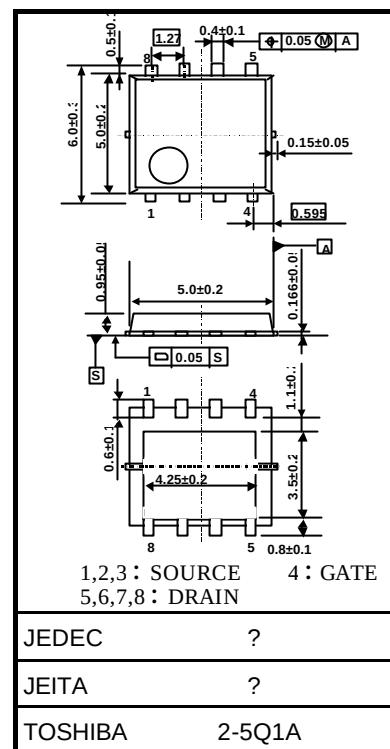
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	100	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	100	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	20	A
	Pulsed (Note 1)	I_{DP}	40	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	45	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2a)		P_D	2.8	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2b)		P_D	1.6	W
Single pulse avalanche energy (Note 3)		E_{AS}	351	mJ
Avalanche current		I_{AR}	20	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	4.5	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: For (Note 1), (Note 2), (Note 3), (Note 4), please refer to the next page.

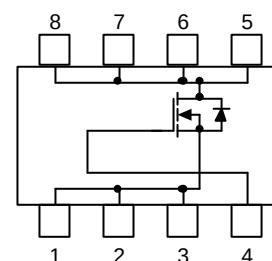
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.080 g (typ.)

Circuit Configuration

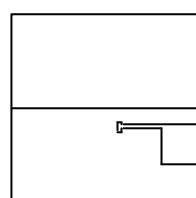


Thermal Characteristics

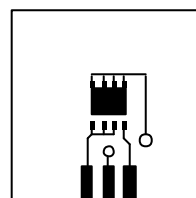
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case ($T_c=25^\circ\text{C}$)	$R_{th(ch-c)}$	2.78	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ($t = 10\text{ s}$) (Note 2a)	$R_{th(ch-a)}$	44.6	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ($t = 10\text{ s}$) (Note 2b)	$R_{th(ch-a)}$	78.1	$^\circ\text{C/W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C .

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)

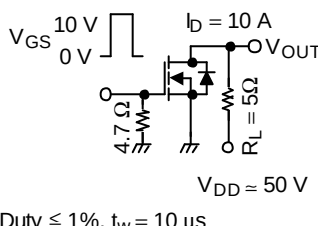


(b)

Note 3: $V_{DD} = 50\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1.0\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = 20\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 100	nA
Drain cut-OFF current		I_{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	100	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	3.0	—	5.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	—	30	47	m Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 10 \text{ A}$	9.5	19	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1000	—	pF
Reverse transfer capacitance		C_{rss}		—	21	—	
Output capacitance		C_{oss}		—	500	—	
Switching time	Rise time	t_r	 $V_{GS} = 10 \text{ V}, 0 \text{ V}$ $I_D = 10 \text{ A}$ $V_{DD} \approx 50 \text{ V}$ $R_L = 5 \Omega$ 47Ω $Duty \leq 1\%, t_w = 10 \mu\text{s}$	—	(2)	—	ns
	Turn-ON time	t_{on}		—	(13)	—	
	Fall time	t_f		—	3	—	
	Turn-OFF time	t_{off}		—	13	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} = 80 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	—	15	—	nC
Gate-source charge 1		Q_{gs1}		—	7.2	—	
Gate-drain ("miller") charge		Q_{gd}		—	5.0	—	
Gate switch charge		Q_{sw}		—	8.5	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (tw=1ms)	I_{DRP}	—	—	—	40	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 20 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V

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